

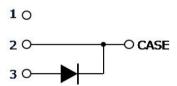
CoolSiC™ Automotive Schottky Diode 650V G5

650V/20A Silicon Carbide Schottky Diode in TO247-3

Features

- Revolutionary semiconductor material Silicon Carbide
- Benchmark switching behavior
- No reverse recovery/ No forward recovery
- Temperature independent switching behavior
- High surge current capability
- Pb-free lead plating; RoHS compliant
- Junction Temperature range from -40°C to 175°C
- System efficiency improvement over Si diodes
- System cost / size savings due to reduced cooling requirements
- Enabling higher frequency / increased power density solutions
- Higher system reliability due to lower operating temperatures
- Reduced EMI





Potential Applications

- Traction inverter
- Booster / DCDC Converter
- On board Charger / PFC









Product Validation

"Qualified for Automotive Applications. Product Validation according to AEC-Q100/101"

Description

The 5th Generation CoolSiCTM Automotive Schottky Diode represents Infineon leading edge technology for Silicon Carbide Schottky Barrier diodes. Thanks to a compact design and a technology based on thin wafers, this family of products shows improved efficiency over all load conditions resulting from both its thermal characteristics and low figure of merit (Qc x Vf). This product family has been designed to complement Infineon's IGBT and CoolMOSTM portfolio. This ensures meeting the most stringent application requirements in the 650V voltage class.

Product Information					
Ordering Code	AIDW20S65C5				
Marking	AD2065C5				
Package	PG-TO247-3-41				
SP Number	SP001725214				

Parameter	Value/Unit				
$V_{DC,max}$	650 V				
I _F ; T _C < 127 °C	20 A				
Q_{C} ; V_{R} = 400 V	29 nC				
E _C ; V _R = 400 V	6.6 μJ				
$T_{j,max}$	175 °C				

Pin	Definition
Pin 2, case	Cathode
Pin 3	Anode



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Maximum Ratings

1 Maximum Ratings

Table 1 Maximum ratings¹

Parameter	Symbol	Value	Unit
Repetitive peak reverse voltage	V_{RRM}	650	V
Continuous forward current for $R_{thJC,max}$ $T_C = 127 ^{\circ}C$, D=1	I _F	20	А
Surge non-repetitive forward current, sine halfwave T_c = 25°C, t_p =10ms T_c = 150°C, t_p =10ms	I _{F,SM}	103 87	А
Non-repetitive peak forward current $T_c=25^{\circ}C$, $t_p=10\mu s$	I _{F,max}	776	А
i^2t value T_c = 25°C, t_p =10ms T_c = 150°C, t_p =10ms	∫i² dt	53 38	A ² s
Diode dv/dt ruggedness V _R =0480V	dv/dt	100	V/ns
Power dissipation $T_C = 25^{\circ}C$	P _{tot}	112	W
Operating temperature	T _j	-40175	°C
Storage temperature	T _{stg}	-55150	°C
ESD Human body model, R= 1.5 k Ω , C = 100 pF Charged device model		8 2	kV
Soldering temperature, wavesoldering only allowed at leads, 1.6mm (0.063 in.) from case for 10 s	T _{sold}	260	°C
Mounting Torque (M3 and M4 screws)		70	Ncm



Thermal Characteristics

2 Thermal Characteristics

Table 2 Thermal Characteristics¹

Parameter	Symbol	Values			Unit	Note /Test condition
Parameter		Min.	Тур.	Мах.	Unit	Note/Test condition
Thermal resistance, junction–case ²	R_{thJC}	-	1.0	1.4	K/W	
Thermal resistance, junction-ambient ²	R _{thJA}	-	-	62	K/W	



Electrical Characteristics

3 Electrical Characteristics

Table 3 Static Characteristics

Parameter	Symbol	Values			l lmit	Note/Test on dition
Parameter		Min.	Тур.	Max.	Unit	Note/Test condition
DC blocking voltage	V _{DC}	650	ı	-		$T_j = 25$ °C, $I_R = 0.12$ mA
Diode forward voltage ³	V _F	-	1.5	1.7	V	$T_j = 25$ °C, $I_F = 20$ A
		-	1.8	2.1		$T_j = 150$ °C, $I_F = 20$ A
Reverse current	I _R	-	3	120		V _R = 650 V, T _j = 25 °C
		-	24	-	μΑ	V _R = 650 V, T _j = 150 °C

Table 4 Dynamic Characteristics at Tj=25°C unless noted otherwise

Parameter	Values		Unit	Note/Test condition		
raiailletei	Symbol	Min.	Тур.	Мах.	Oill	Note/Test condition
Total capacitive charge	Q _c	-	29	-	nC	$V_R = 400 \text{ V}, \text{ di/dt} = 200 \text{ A/}\mu\text{s},$ $I_F \le I_{F,MAX}, T_j = 150 \text{ °C}$
Total capacitance	С	-	584	-	pF	V _R = 1 V, f = 1 MHz
		-	76	-		V _R = 300 V, f= 1 MHz
		-	75	-		V _R = 600 V, f= 1 MHz

Footnotes:

¹ The parameter is not subject to production test- verified by design/characterization.

² Rth,JC defined as per JESD-51-14. Rth,JA defined as per JESD-51-2.

³ Only the value at 25°C is subject to production test. The value at 150°C is only verified by design/characterization.



Electrical Characteristics Diagrams

4 Electrical Characteristics Diagrams

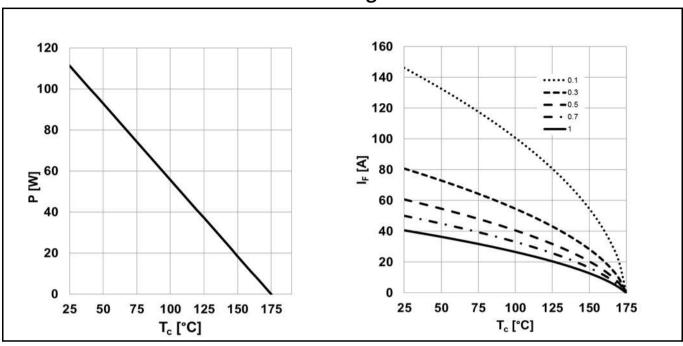


Figure 1 (LEFT) Power dissipation; $P_{tot} = f(T_C)$; $R_{thJC,max}$ (RIGHT) Diode forward current; $I_F = f(T_C)$; $T_i \le 175$ °C; $R_{thJC,max}$; parameter: D=duty cycle

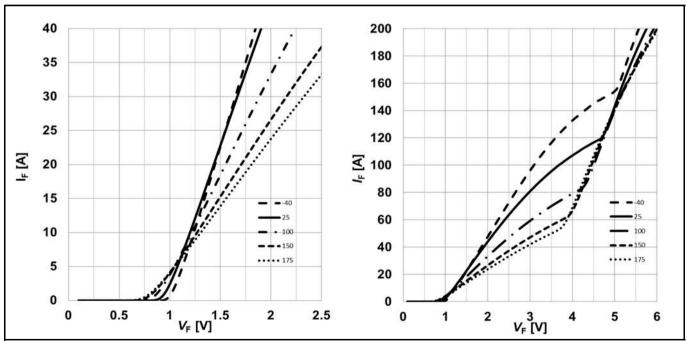


Figure 2 (LEFT) Typical forward characteristic; $I_F = f(V_F)$; $t_P = 200 \,\mu s$; parameter: T_j (RIGHT) Typical forward characteristics in surge current; $I_F = f(V_F)$; $t_P = 200 \,\mu s$; parameter: T_j



Electrical Characteristics Diagrams

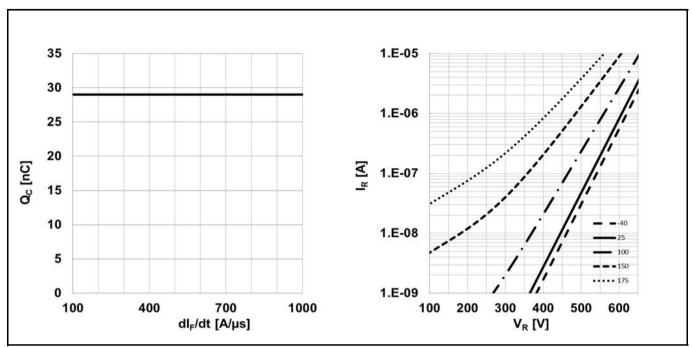


Figure 3 (LEFT) Typical capacitive charge versus current slope (only capacitive charge, guaranteed by design); $Q_C = f(di_F/dt)$; $T_j = 150^{\circ}C$; $V_R = 400V$; $I_F \le I_{F,max}$ (RIGHT) Typical reverse current versus reverse voltage; $I_R = f(V_R)$; parameter: T_i

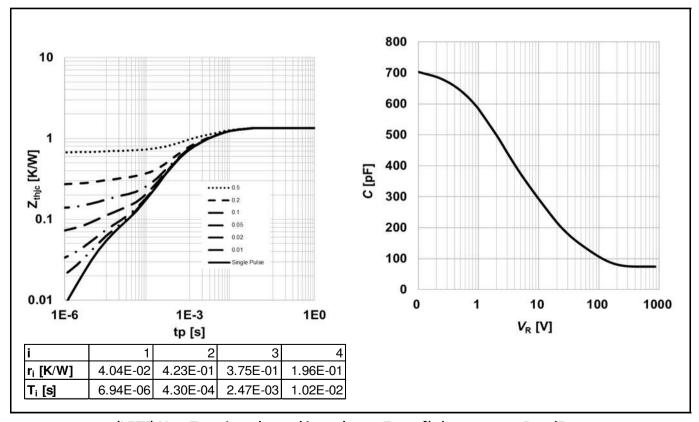


Figure 4 (LEFT) Max. Transient thermal impedance; $Z_{thJC} = f(t_p)$; parameter: $D = t_p/T$ (RIGHT) Typ. Capacitance vs. Reverse voltage; $C = f(V_R)$; $T_i = 25^{\circ}C$; f = 1 MHz



Electrical Characteristics Diagrams

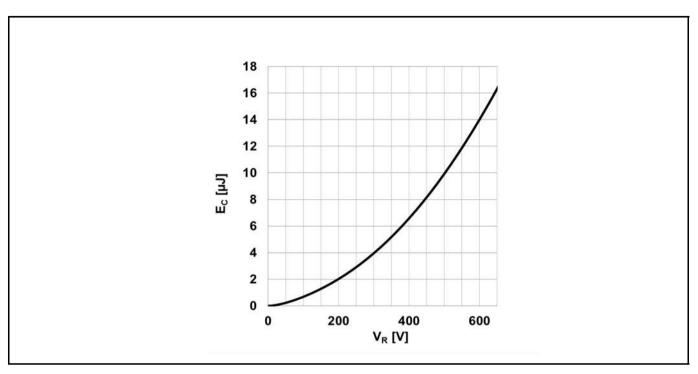


Figure 5 Typical capacitance stored energy; $E_C = f(V_R)$

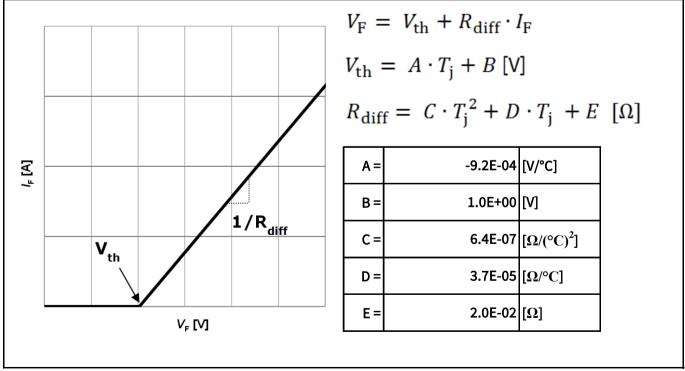


Figure 6 Simplified forward characteristics model $V_F = f(I_F)$; -40°C < T_i < 175°C; I_F < 40 A



Package Outlines

5 Package Outlines

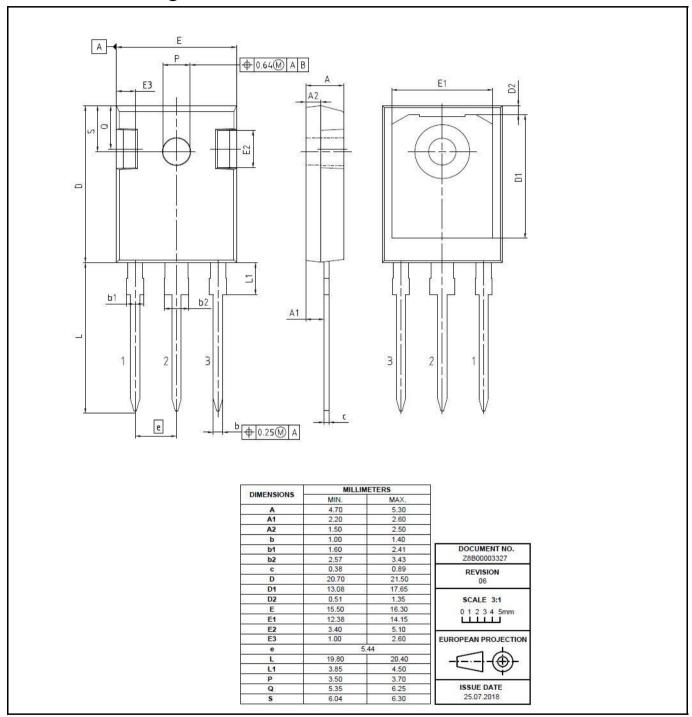


Figure 6 Package outline of PG-TO247-3-41 leaded (Dimensions in mm)



Revision History

Revision History

Document Version	Date of Release	Description of changes			
V3.0	26.11.2018	1st release of Data Sheet			



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Document reference

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